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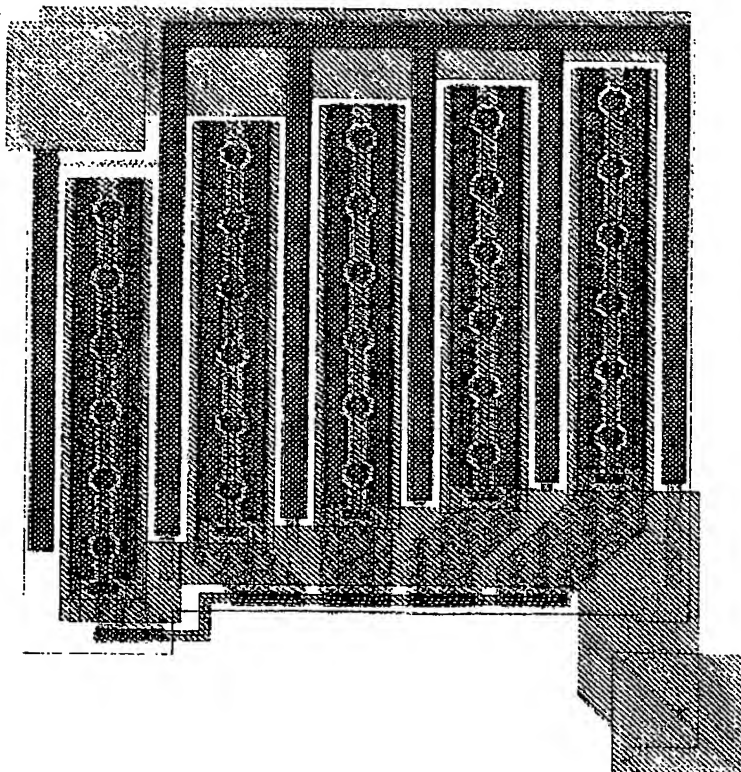
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(54) Title: SEMICONDUCTOR COMPONENT WITH A BIPOLAR LATERAL POWER TRANSISTOR



(57) Abstract: A semiconductor component comprising at least one lateral bipolar power transistor which is composed of at least one group of single transistors with a common collector-, base- and emitter zone, which are parallel connected by three conductor track systems which bring together the emitter-, base- and collector currents of each of the single transistors; and each single transistor comprises an emitter region having an emitter-contact zone with an emitter contact, at least one active emitter zone and a connection zone between the contact zone and the active zone, a base region having a base-contact zone with a base contact and an internal base series resistor, and a collector region, said internal base series resistor being a structured semiconductor region comprising at least two ring segments, which is connected to the base contact zone and to the base contact.

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